

## **CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the present application.

### **Listing of Claims:**

**Claim 1 (previously presented):** A gallium-nitride semiconductor substrate having a mirrorlike, planar surface directly onto which a light-emitting-device-forming film has been epitaxially grown, the gallium-nitride substrate therein contaminated at the interface between the mirrorlike, planar surface and the device-forming film grown thereon by one or more elements selected from Si, Cr, Mn, Fe, Ni, Cu, Zn and Al at a density level of from  $15 \times 10^{10}$  to  $10 \times 10^{11}$  atoms/cm<sup>2</sup>.

**Claim 2 (previously presented):** A gallium-nitride semiconductor substrate having a mirrorlike, planar surface directly onto which a light-emitting-device-forming film has been epitaxially grown, the gallium-nitride substrate therein contaminated at the interface between the mirrorlike, planar surface and the device-forming film grown thereon by one or more elements selected from Si, Cr, Mn, Fe, Ni, Cu, Zn and Al at a density level of from  $15 \times 10^{10}$  to  $5 \times 10^{11}$  atoms/cm<sup>2</sup>.

**Claim 3 (withdrawn):** A method of processing a gallium-nitride semiconductor substrate, the method comprising:

providing a gallium-nitride semiconductor substrate having a complex front side in which the Ga and N faces are exposed in alternation;

polishing the substrate front side with an abrasive embedded into a metallic platen, thereby transforming the substrate episurface into a process-transformed layer;

reactive-ion etching the substrate front side using a halogen plasma to remove the process-transformed layer; and

wet etching the reactive-ion etched substrate, by means of an etchant that is one of  $\text{HF} + \text{H}_2\text{O}_2$ ,  $\text{HCl} + \text{H}_2\text{O}_2$ ,  $\text{H}_2\text{SO}_4 + \text{H}_2\text{O}_2$ ,  $\text{HNO}_3 + \text{H}_2\text{O}_2$ ,  $\text{HF} + \text{O}_3$ ,  $\text{HCl} + \text{O}_3$ ,  $\text{H}_2\text{SO}_4 + \text{O}_3$ ,  $\text{HNO}_3$ , or  $\text{HNO}_3 + \text{O}_3$ , and that has an oxidation-reduction potential of more than 1.2 V, in a room-temperature aqueous solution of pH = 2 to 3, thereby to remove contaminant metal produced by said reactive-ion etching.

**Claim 4 (canceled)**

**Claim 5 (withdrawn):** A method of processing a gallium-nitride semiconductor substrate as set forth in claim 3, characterized in that a wash for taking off organic matter by means of an organic solvent, and a wash by means of an alkaline solution in order to take off nonmetal contaminants are carried out either before or after the wet etching.

**Claims 6-10 (canceled)**

**Claim 11 (previously presented):** A gallium-nitride semiconductor substrate as set forth in claim 1, wherein the substrate surface on which the device-forming epitaxial film has been grown is a complex of faces in which Ga is exposed, and faces in which N is exposed.

**Claim 12 (previously presented):** A gallium-nitride semiconductor substrate as set forth in claim 2, wherein the substrate surface on which the device-forming epitaxial film has been grown is a complex of faces in which Ga is exposed, and faces in which N is exposed.

**Claims 13 and 14 (canceled)**